

N-channel TrenchMOS standard level FET 11 September 2012

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in a SOT78 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant •
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C •

1.3 Applications

- 12V, 24V and 48V Automotive systems
- Electric and electro-hydraulic power steering •
- Motors, lamps and solenoid control •
- Start-Stop micro-hybrid applications
- Transmission control •
- Ultra high performance power switching •

1.4 Quick reference data

		-					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	80	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	349	W
Static chara	acteristics		1	1			
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11		-	3.3	4	mΩ
Dynamic cl	haracteristics			1			
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I _D = 25 A; V _{DS} = 64 V; Fig. 13; Fig. 14		-	51	-	nC

Quick reference data Table 1

[1] Continuous current is limited by package.

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2. Pinning information

Table 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	G	gate	mb	D			
2	D	drain					
3	S	source		G-UF-4			
mb	D	mounting base; connected to drain	TO-220AB (SOT78A)	mbb076 Ś			

3. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BUK753R8-80E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A				

4. Marking

Table 4. Marking codes	
Type number	Marking code
BUK753R8-80E	BUK753R8-80E

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

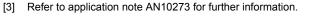
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	80	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	80	V
V _{GS}	gate-source voltage	T _j = 175 °C; DC		-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	120	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	120	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	758	А

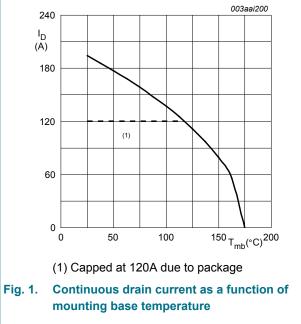
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Symbol	Parameter	Conditions		Min	Max	Unit	
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	349	W	
T _{stg}	storage temperature			-55	175	°C	
Tj	junction temperature			-55	175	°C	
Source-drain diode							
I _S	source current	T _{mb} = 25 °C	[1]	-	120	А	
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	758	А	
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 120 \text{ A}; V_{sup} \leq 80 V; \text{R}_{GS} = 50 \Omega; \\ V_{GS} &= 10 V; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ \hline \text{Fig. 3} \end{split}$	[2][3]	-	488	mJ	

Continuous current is limited by package. [1]

Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. Refer to application note AN10273 for further information. [2]





 $V_{GS} \ge 10V$

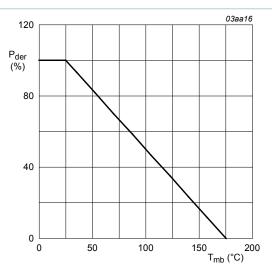
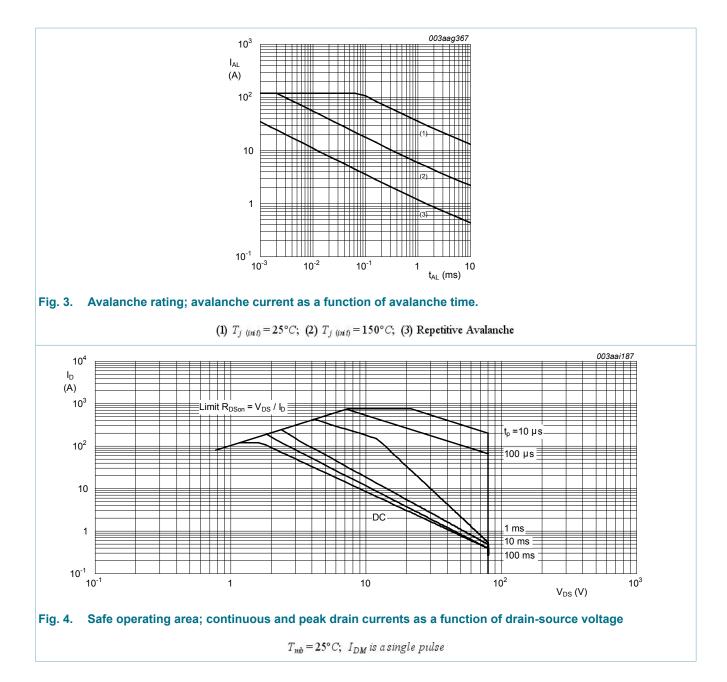


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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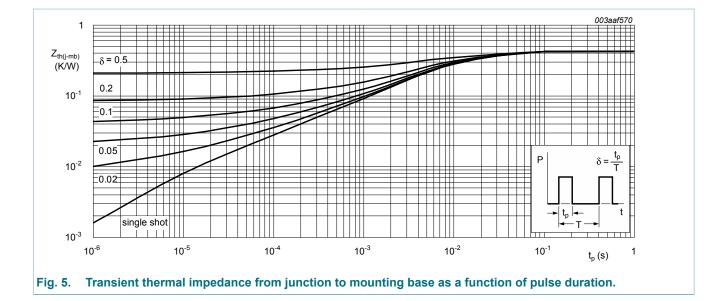


6. Thermal characteristics

Table 6. Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5		-	-	0.43	K/W	
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in still air		-	60	-	K/W	

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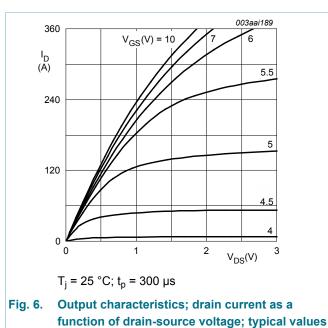
Characteristics 7.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·	I			
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	80	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	72	-	-	V
V _{GS(th)}	GS(th) gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	1	-	-	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	4.5	V	
I _{DSS}	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	0.15	2	μA
		V_{DS} = 80 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	3.3	4	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	9.7	mΩ
Dynamic ch	naracteristics	· · ·	1			
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 64 V; V _{GS} = 10 V;	-	169	-	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	37	-	nC
Q _{GD}	gate-drain charge	1	-	51	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	9020	12030	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	840	1010	pF
C _{rss}	reverse transfer capacitance		-	470	645	pF
t _{d(on)}	turn-on delay time	V_{DS} = 60 V; R _L = 2.4 Ω; V _{GS} = 10 V;	-	38	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	48	-	ns
t _{d(off)}	turn-off delay time		-	129	-	ns
t _f	fall time		-	65	-	ns
L _D	internal drain inductance	from drain lead 6mm from package to centre of die	-	4.5	-	nH
		from upper edge of mounting base to centre of die	-	2.5	-	nH
L _S	internal source inductance	from source lead to source bond pad	-	7.5	-	nH
Source-dra	iin diode	· · ·	1			
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.77	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	58	-	ns
Qr	recovered charge	V _{DS} = 25 V	-	121	-	nC



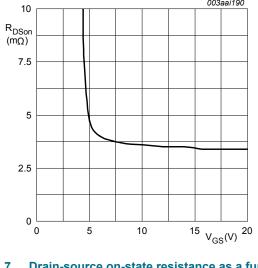
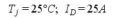


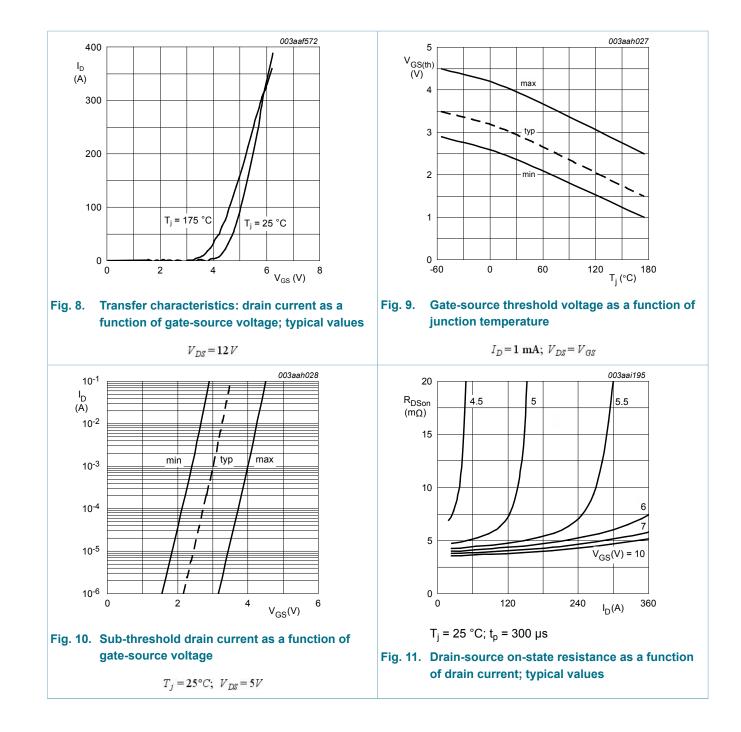
Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



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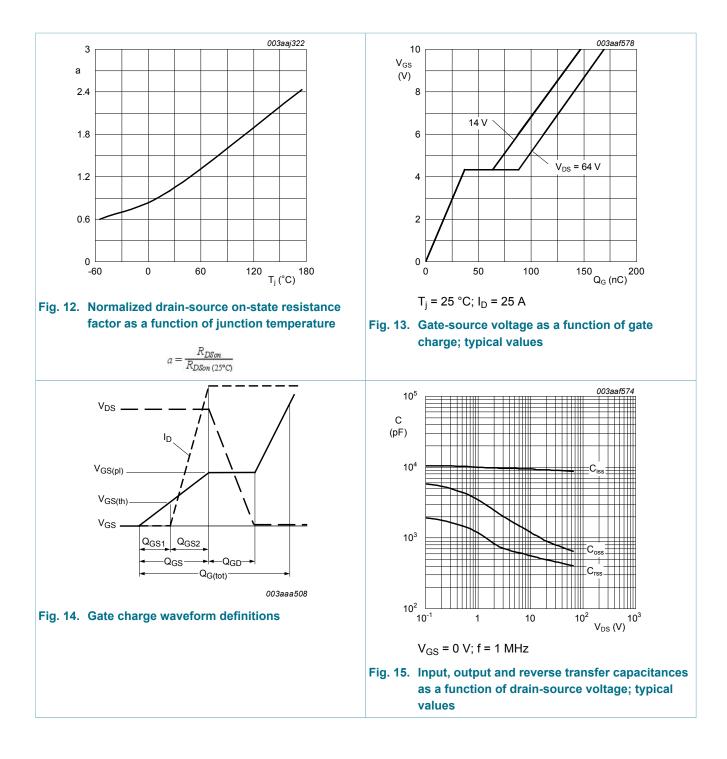
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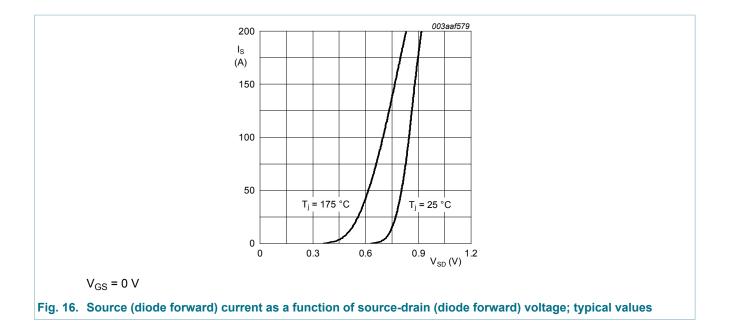
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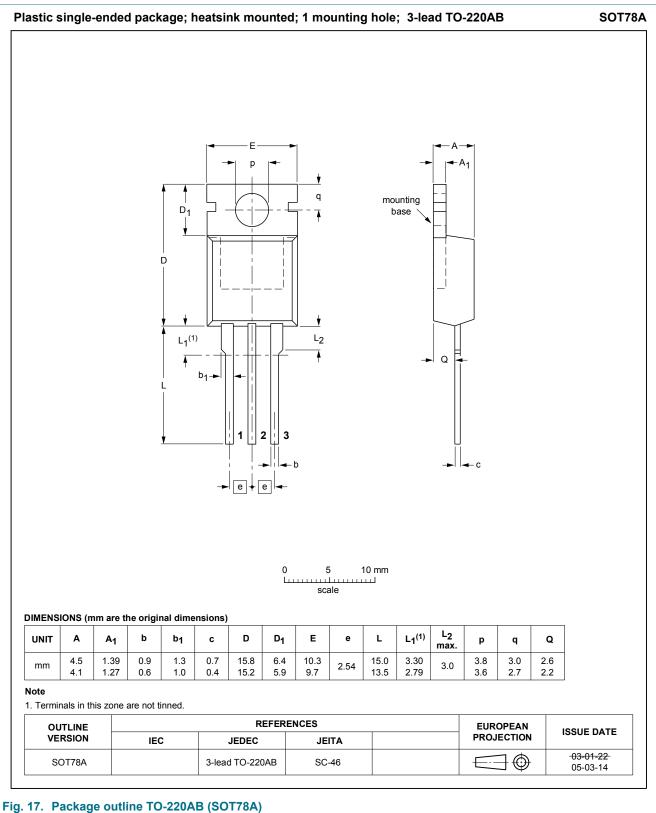
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8. Package outline



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9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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